



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		Atty. Docket SUND 466		Application No. 10/603,659			
		Applicant Mu-Jen LAI et al.					
		Filing Date June 26, 2003		Group 2814			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub- Class	Trans- lation
	AI						
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM	"ZnTe-GaN heterostructure switching device", A. G. Drizhuk et al.; Tech. Phys. Lett. 23 (10), October 1997; 1997 American Institute of Physics; pages 809 and 810					
	AN	"Growth of GaN on Si substrates - roles of BP thin layer" Optical Materials, S. Nishimura et al.; one page - ISI Web of Science 6.0					
Examiner <i>Mjm</i>					Date Considered 8-12-04		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							